

Silicon Carbide Schottky Diode 1200 V, 20 A, 89 nC

General Description

This product family is CRM's second generation SiC JBS, with lower VF and offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required. It is qualified and manufactured on the productive 6 inch SiC line in China fully owned by CR MICRO.

Features

- \bullet Low conduction loss due to low $V_{\rm F}$
- \bullet Extremely low switching loss by tiny Q_{C}
- Highly rugged due to better surge current
- Industrial standard quality and reliability

Applications

- Solar inverter
- EV charge
- High performance SMPS
- Power factor correction



V _{RRM}	1200 V
I _F (T _C =159℃)	20 A
Q _C	89 nC







Equivalent circuit



Package Marking and Ordering Information

Part #	Marking	Package
CRXU20D120G2	CRXU20D120G2	TO-247-2





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Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	1200	V
Surge Peak Reverse Voltage	V _{RSM}	1200	V
DC Peak Reverse Voltage	V _R	1200	V
Continuous Forward Current			
$T_c = 25^{\circ}C$	т	63	٨
T _c = 135°C	1 _F	32	A
$T_{\rm C} = 159^{\circ}{\rm C}$		20	
Non-Repetitive Forward Surge Current			
$T_{C} = 25^{\circ}C, t_{p} = 8.3 \text{ms}, \text{Half Sine Pulse}$	I _{FSM}	160	А
$T_{C} = 110^{\circ}C, t_{p} = 8.3 \text{ms}, \text{Half Sine Pulse}$		140	
Non-Repetitive Forward Surge Current			
$T_{C} = 25^{\circ}C, t_{p} = 8.3 \text{ms}, \text{Half Sine Pulse}$	∫ i ² dt	106	A ² s
$T_{C} = 110^{\circ}C, t_{p} = 8.3 \text{ms}, \text{Half Sine Pulse}$		81	
Power dissipation			
$T_c = 25^{\circ}C$	P _{tot}	214	W
$T_{C} = 110^{\circ}C$		93	
Operating junction Range	Tj	-55 to +175	°C
Storage temperature Range	${\cal T}_{\sf stg}$	-55 to +150	°C

Maximum Ratings (at Tc = 25 °C, unless otherwise specified)





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Thermal Resistance

Parameter	Symbol	Max.	Unit
Thermal resistance, junction – case.	R_{thJC}	0.7	°C/W

Electrical Characteristic (at Tc = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition	
Farameter	Symbol	min.	typ.	max.	Unit	Test condition	
						I _F =20A	
Forward Voltage	V _F	-	1.4	1.7	V	T _j =25°C	
		-	2	-		T _j =175°C	
					μA	V _R =1200V	
Reverse Current	I _R	-	5	100		T _j =25°C	
		-	50	-		T _j =175°C	
Total Capacitive Charge	Q _c				nC	V_{R} =800V, T_{j} =25°C	
		-	89	-		$Q_C = \int_0^{V_R} C(V) dV$	
Total Capacitance	С					T _j =25℃, f=1MHz	
		-	1320	-	pF	V _R =0V	
		-	86	-		V _R =400V	
		-	69	-		V _R =800V	





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Characteristics Curve:



Fig 3: Current Derating



Fig 5: Capacitance vs. Reverse Voltage

















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Fig 7: Typical Capacitance Stored Energy







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Package Outline: TO-247-2



Itoma	Values(mm)			
Items	MIN	MAX		
А	4.85	5.15		
A1	2.25	2.55		
A2	1.85	2.15		
В	1.04	1.33		
B1	1.90	2.35		
B2	1.90	2.15		
С	0.55	0.68		
D	20.80	21.10		
D1	16.25	17.65		
D2	0.95	1.35		
E	15.70	16.10		
E1	13.50	14.20		
E2	3.80	5.00		
E3	1.00	2.60		
е	10.63	11.13		
L	19.80	20.30		
L1	4.00	4.50		
φΡ	3.50	3.70		
Q	5.40	6.00		
S	6.00	6.40		





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Revision History

Revison	Date	Major changes
1.0		Release of formal version.

Warnings

Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximun ratings of the device.

1. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.

2. This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.



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